



JN180G10HJ

N-Channel Enhancement Mode Field Effect Transistor

Product Summary

V_{DS}	100V
I_D	180A
$R_{DS(ON)}$ (at $V_{GS}=10V$)	4.3m
100% EAS Tested	
100%	



Typical Electrical and Thermal Characteristics Diagrams

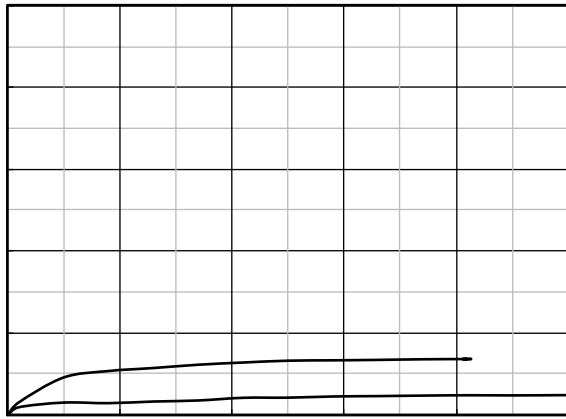


Figure 1. Output Characteristics

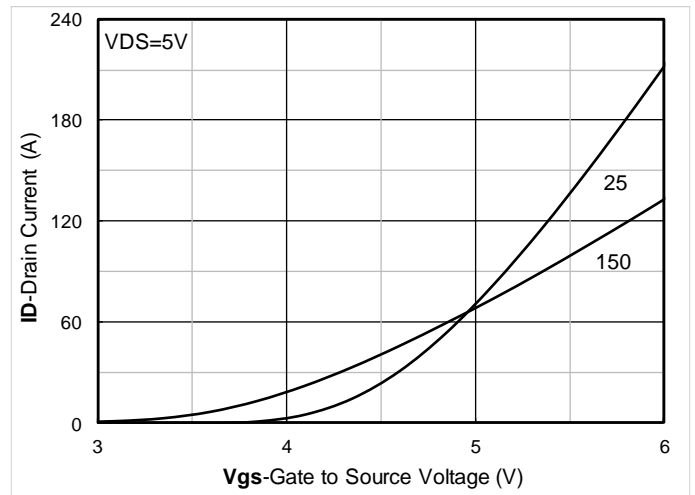


Figure 2. Transfer Characteristics



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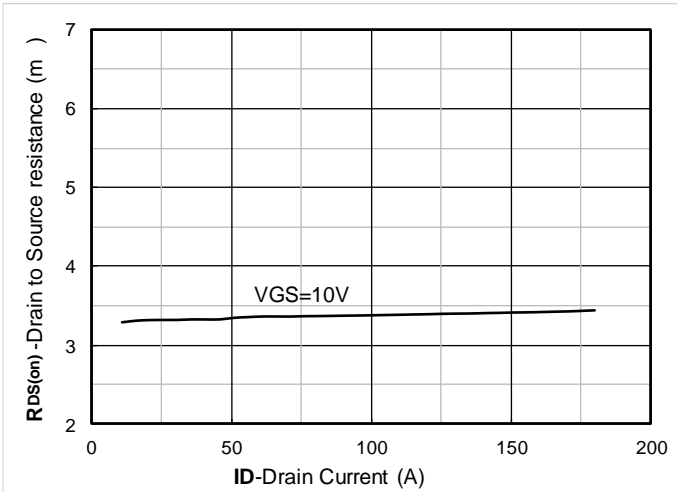


Figure 7. $R_{DS(on)}$ VS Drain Current

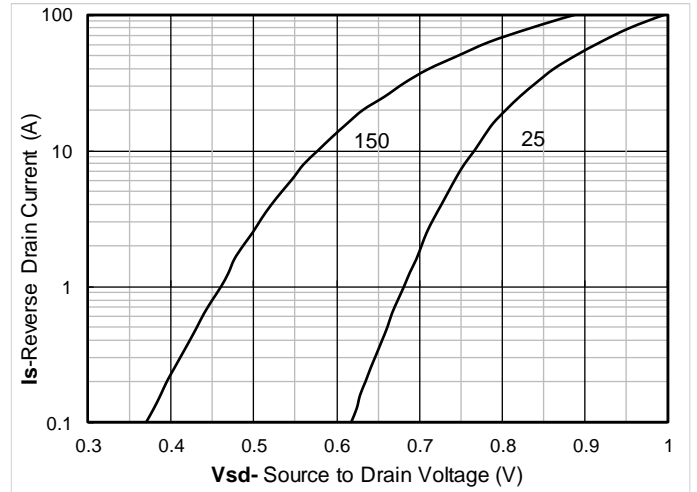


Figure 8. Forward characteristics of reverse diode

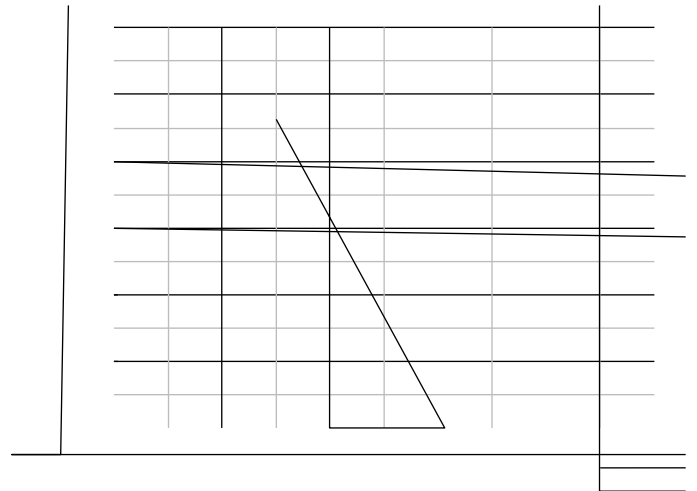


Figure 9. Normalized breakdown voltage

Figure 10. Normalized Threshold voltage

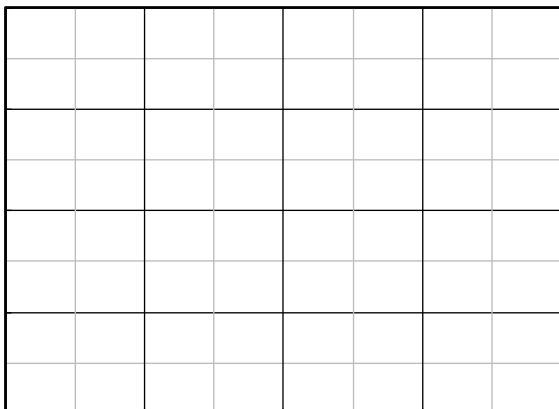


Figure 11. Current dissipation

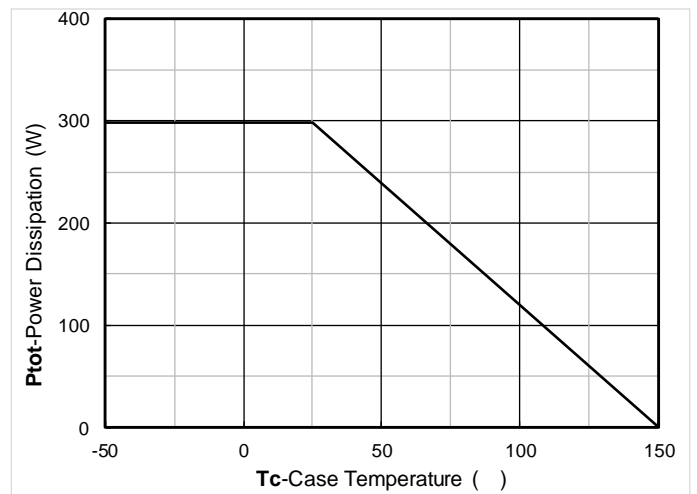


Figure 12. Power dissipation

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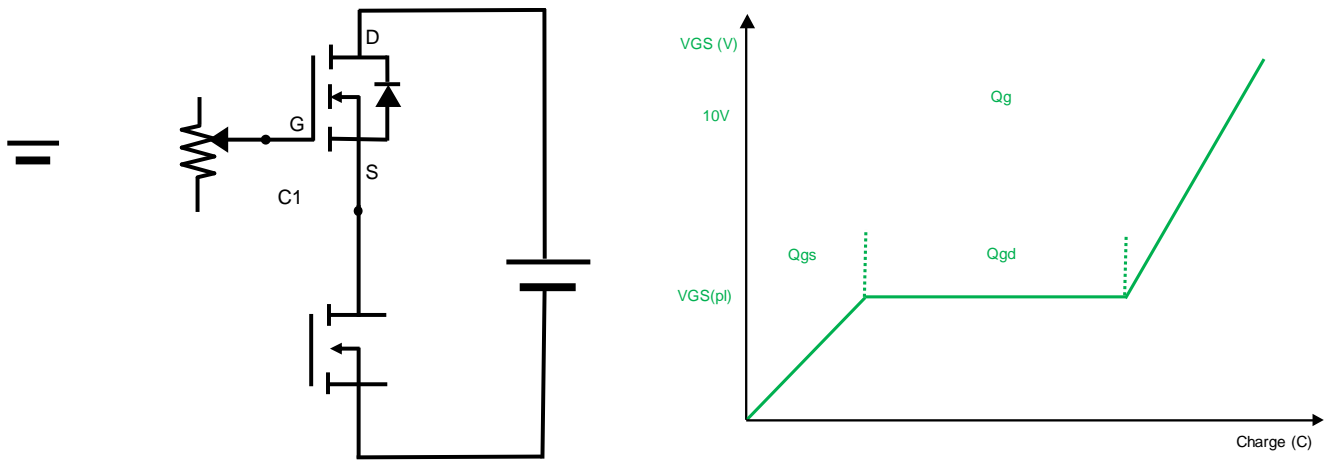


Figure B. Gate Charge Test Circuit & Waveform

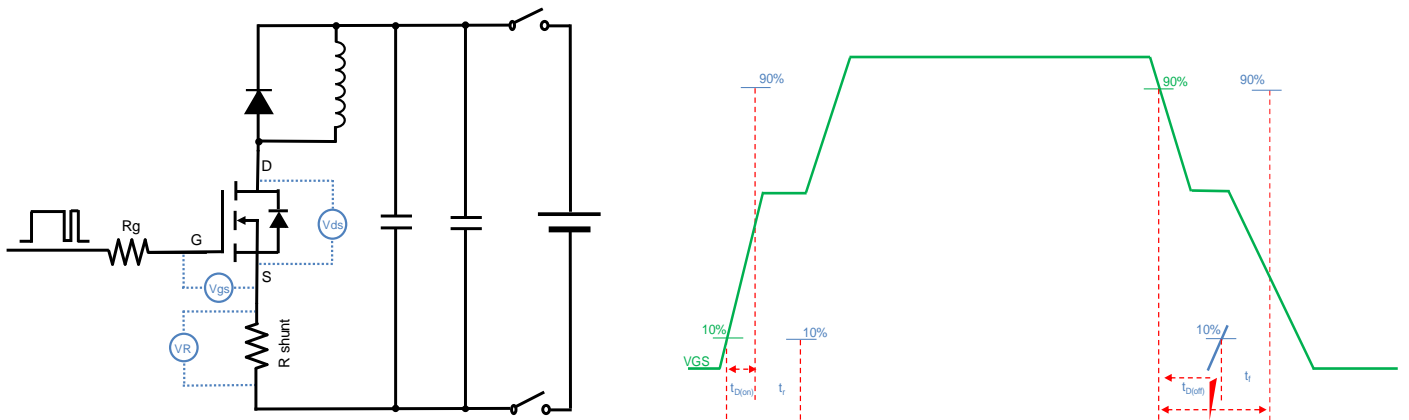


Figure C. Resistive Switching Test Circuit & Waveform



Figure D. Diode Recovery Test Circuit & Waveform



TO-247AB Package information

TO-247AB	
Dim	Min



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